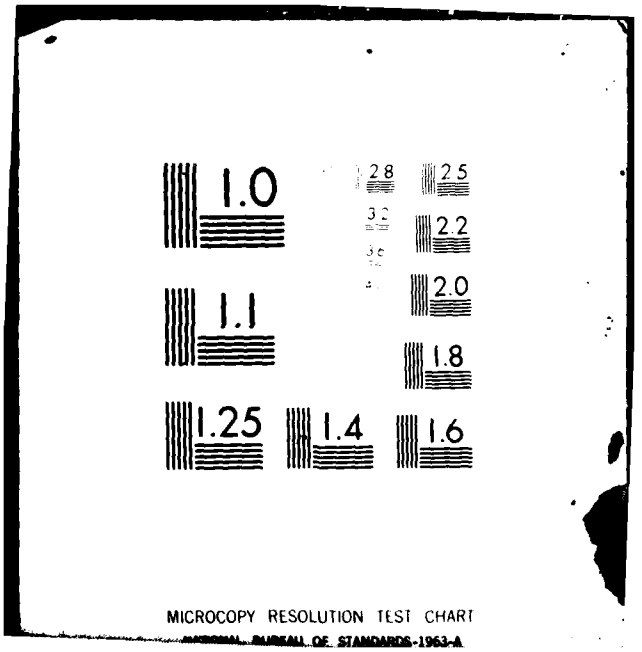
AD-A112 161 FOREIGN TECHNOLOGY DIV WRIGHT-PATTERSON AFB OH F/G 13/7
MEMORY DEVICE,(U)
MAR 82 N A PASHKIN, V N MALYUTIN
UNCLASSIFIED FTD-ID(RS)T-0163-82 NL


1.0
1.1
1.25
1.4
1.6
2.0
1.8
2.2
2.5
MICROCOPY RESOLUTION TEST CHART
NATIONAL BUREAU OF STANDARDS-1963-A

FTD-ID(RS)T-0163-82

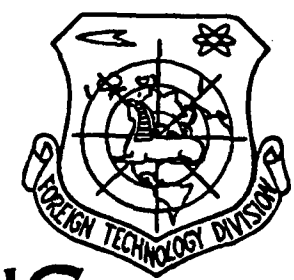
AD A112161

FOREIGN TECHNOLOGY DIVISION

MEMORY DEVICE

by

N.A. Pashkin, V.N. Malyutin and V.V. Yefremov



Approved for public release;
distribution unlimited.

EDITED TRANSLATION

FTD-ID(RS)T-0163-82 3 March 1982

MICROFICHE NR: FTD-82-C-000275

MEMORY DEVICE

By: N.A. Pashkin, V.N. Malyutin and V.V. Yefremov

English pages: 2

Source: USSR Patent Nr. 196457, 16 May 1967, pp. 1-2

Country of origin: USSR
Translated by: Victor Mesenzeff
Requester: USAMICOM

PREPARED BY:

TRANSLATION DIVISION
FOREIGN TECHNOLOGY DIVISION
WP-AFB, OHIO.

U. S. BOARD ON GEOGRAPHIC NAMES TRANSLITERATION SYSTEM

Block	Italic	Transliteration	Block	Italic	Transliteration
А а	*А а*	A, a	Р р	*Р р*	R, r
Б б	*Б б*	B, b	С с	*С с*	S, s
В в	*В в*	V, v	Т т	*Т т*	T, t
Г г	*Г г*	G, g	У у	*У у*	U, u
Д д	*Д д*	D, d	Ф ф	*Ф ф*	F, f
Е е	*Е е*	Ye, ye; E, e*	Х х	*Х х*	Kh, kh
Ж ж	*Ж ж*	Zh, zh	Ц ц	*Ц ц*	Ts, ts
З з	*З з*	Z, z	Ч ч	*Ч ч*	Ch, ch
И и	*И и*	I, i	Ш ш	*Ш ш*	Sh, sh
Й й	*Й й*	Y, y	Щ щ	*Щ щ*	Shch, shch
К к	*К к*	K, k	Ъ ъ	*Ъ ъ*	"
Л л	*Л л*	L, l	Ы ы	*Ы ы*	Y, y
М м	*М м*	M, m	Ь ь	*Ь ь*	'
Н н	*Н н*	N, n	Э э	*Э э*	E, e
О о	*О о*	O, o	Ю ю	*Ю ю*	Yu, yu
П п	*П п*	P, p	Я я	*Я я*	Ya, ya

*ye initially, after vowels, and after ъ, ь; e elsewhere.
When written as ё in Russian, transliterate as yё or ё.

RUSSIAN AND ENGLISH TRIGONOMETRIC FUNCTIONS

Russian	English	Russian	English	Russian	English
sin	sin	sh	sinh	arc sh	$\sinh^{-1}$
cos	cos	ch	cosh	arc ch	$\cosh^{-1}$
tg	tan	th	tanh	arc th	$\tanh^{-1}$
ctg	cot	cth	coth	arc cth	$\coth^{-1}$
sec	sec	sch	sech	arc sch	sech^{-1}
cosec	csc	csch	csch	arc csch	csch^{-1}

Russian	English
rot	curl
lg	log

MEMORY DEVICE

N. A. Pashkin, V. N. Malyutin
and V. V. Yefremov

There are memory devices built of the elements of pneumoautomatics.

The memory device being proposed is based on the change in resistance to the jet flowing from a nozzle, and is different from the existing devices in that to ensure the possibility of an immediate rewrite of information and its long-term storage with a zero expenditure of compressed gas, its carrier of information is made in the form of a film or a layer of an elastic material (for example, rubber) with cone-shaped projections and is located between the pusher of the recording mechanism and the read nozzle, which serves also as the erasure mechanism.

The structural scheme of the device is shown by the drawing.

It contains the information carrier 1 with cone-shaped projections, pusher 2 of the recording mechanism, recoil spring 3, read nozzle 4, recoil spring 5, pushing component 6 of the erasure mechanism, flexible element 7 of a pneumatic drive to the nozzle, and guide rack 8.

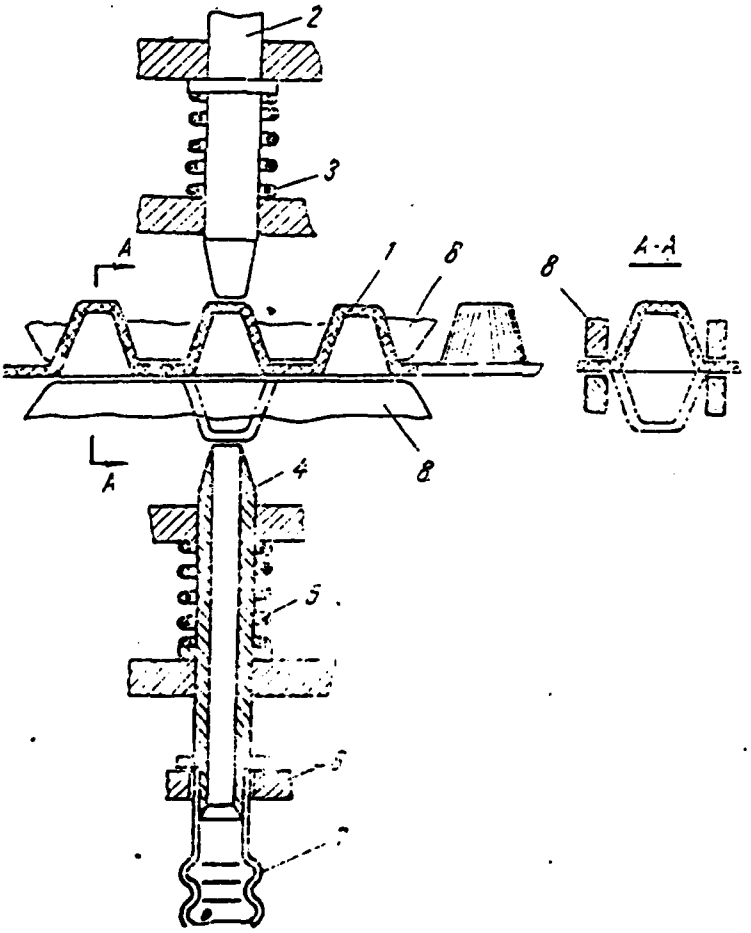
The information carrier is made in the form of a film or a layer of an elastic material (for, example, rubber) with cone-shaped projections, which are pushed out during the recording (erasing) of information by means of the pushers from different sides of the carrier and, depending on the position, they either close or leave the input of the read nozzle open during the read mode.

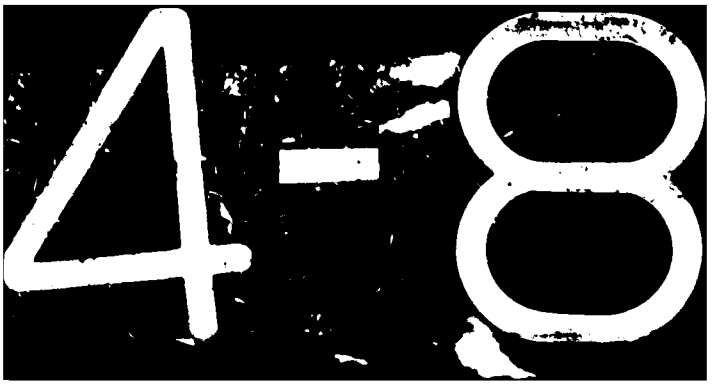
In order to ensure an immediate check and rewrite of information,

ısher of the recording mechanism and the read nozzle of each of ıts are on the same axis; in this case, the latter serves simultaıy as the pusher of the erasure mechanism.

t Claims

ıe memory device for the pneumatic-automatics systems, which con- a carrier of information, a mechanism for its displacement, and ıisms for recording, erasing, reading of information, is **different** at to ensure the possibility of an immediate rewrite of information ts long-term storage with a zero expenditure of compressed gas, nformation carrier is made in the form of a film or a layer of an ic material (for example, rubber) with cone-like projections and ranged between the pusher of the recording mechanism and the read e, which also is the pusher of the erasure mechanism.




4-8